

**SFF75N10M**  
**SFF75N10Z**

14849 Firestone Boulevard · La Mirada, CA 90638  
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

**Designer's Data Sheet**

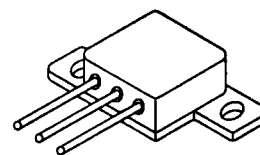
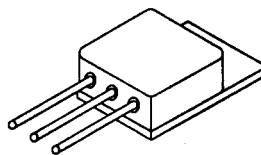
**FEATURES:**

- Rugged construction with polysilicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Ceramic Seals for improved hermeticity
- Hermetically sealed package
- TX, TXV and Space Level screening available
- Replaces: IXTH75N10 Types

**75 AMP**  
**100 VOLTS**  
**0.025 Ω**  
**N-CHANNEL**  
**POWER MOSFET**

TO-254

TO-254Z

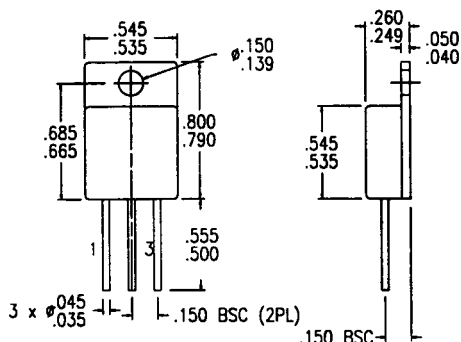


**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V <sub>DS</sub>	100	Volts
Gate to Source Voltage	V <sub>GS</sub>	±20	Volts
Continuous Drain Current	I <sub>D</sub>	75	Amps
Operating and Storage Temperature	T <sub>op</sub> & T <sub>stg</sub>	-55 to +150	°C
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	0.83	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P <sub>D</sub>	150 114	Watts
Repetitive Avalanche Energy	EAR	30	mJ

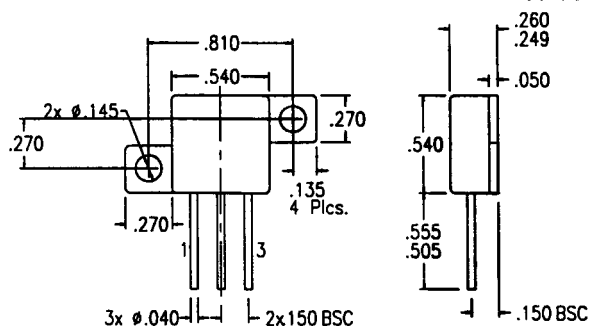
**PACKAGE OUTLINE: TO-254**

**PIN OUT:**  
**PIN 1: DRAIN**  
**PIN 2: SOURCE**  
**PIN 3: GATE**



**PACKAGE OUTLINE: TO-254Z**

**PIN OUT:**  
**PIN 1: DRAIN**  
**PIN 2: SOURCE**  
**PIN 3: GATE**



Available with Glass or Ceramic Seals. Contact Factory for details.

**NOTE:** All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

**DATA SHEET #: F00153 D**

**MED**

**SFF75N10M**  
**SFF75N10Z**

PRELIMINARY



**SOLID STATE DEVICES, INC**

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**ELECTRICAL CHARACTERISTICS @ T<sub>J</sub>=25°C (Unless Otherwise Specified)**

RATING	SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V <sub>GS</sub> =0 V, I <sub>D</sub> =250μA)	BV <sub>DSS</sub>	100	---	---	V
Drain to Source on State Resistance (V <sub>GS</sub> =10 V) ID=37.5A ID=75 A	R <sub>DS(on)</sub>	---	---	0.025 0.030	Ω
On State Drain Current (V <sub>DS</sub> > I <sub>D(on)</sub> X R <sub>DS(on)</sub> Max, V <sub>GS</sub> =10 V)	I <sub>D(on)</sub>	75	---	---	A
Gate Threshold Voltage (V <sub>DS</sub> ≥ V <sub>GS</sub> , I <sub>D</sub> =4mA)	V <sub>GS(th)</sub>	2.0	---	4.0	V
Forward Transconductance (V <sub>DS</sub> > I <sub>D(on)</sub> X R <sub>DS(on)</sub> Max, I <sub>DS</sub> =50% rated ID)	g <sub>fs</sub>	25	30	---	S(Ω)
Zero Gate Voltage Drain Current (V <sub>DS</sub> =max rated voltage, V <sub>GS</sub> =0 V) (V <sub>DS</sub> =80% rated V <sub>DS</sub> , V <sub>GS</sub> =0 V, T <sub>A</sub> =125°C)	I <sub>DSS</sub>	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	I <sub>GSS</sub>	---	---	+200 -200	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	---	160 16 50	260 70 160	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	---	30 35 100 40	40 100 120 80	nsec
Diode Forward Voltage (I <sub>S</sub> =rated ID, V <sub>GS</sub> =0 V, T <sub>J</sub> =25°C)	V <sub>SD</sub>	---	1.3	1.75	V
Diode Reverse Recovery Time Reverse Recovery Charge	t <sub>rr</sub> Q <sub>RR</sub>	---	120 ---	200 ---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	---	4500 1600 800	---	pF

SAFE OPERATING AREA (S.O.A.)  
T<sub>C</sub> = 25 C, D.C. CONDITION

